# MOSFET – Power, Single N-Channel, SO-8 FL

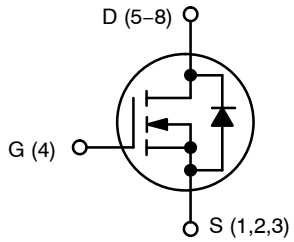
## 30 V, 127 A

## NVMFS4C05N, NVMFS4C305N

| $V_{(BR)DSS}$ | $R_{DS(ON)}$ MAX | $I_D$ MAX |
|---|---|---|
| 30 V | 2.8 mΩ @ 10 V | 127 A |
| | 4.0 mΩ @ 4.5 V | |

### Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Optimized Gate Charge to Minimize Switching Losses
- NVMFS4C05NWF – Wettable Flanks Option for Enhanced Optical Inspection
- AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant



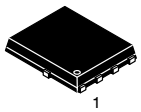

**N–CHANNEL MOSFET**

**MAXIMUM RATINGS** ($T_J$ = 25°C unless otherwise stated)

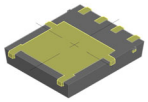
| Parameter | | | Symbol | Value | Unit |
|---|---|---|---|---|---|
| Drain–to–Source Voltage | | | $V_{DSS}$ | 30 | V |
| Gate–to–Source Voltage | | | $V_{GS}$ | ±20 | V |
| Continuous Drain Current $R_{\theta JA}$ (Notes 1, 2 and 4) | Steady State | $T_A$ = 25°C | $I_D$ | 27.2 | A |
| | | $T_A$ = 80°C | | 21.6 | |
| Power Dissipation $R_{\theta JA}$ (Notes 1, 2 and 4) | | $T_A$ = 25°C | $P_D$ | 3.61 | W |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3 and 4) | | $T_C$ = 25°C | $I_D$ | 127 | A |
| Continuous Drain Current $R_{\theta JC}$ (Notes 1, 2, 3 and 4) | | $T_C$ = 80°C | | 101 | |
| Power Dissipation $R_{\theta JC}$ (Notes 1, 2, 3 and 4) | | $T_C$ = 25°C | $P_D$ | 79 | W |
| Pulsed Drain Current | $T_A$ = 25°C, $t_p$ = 10 μs | | $I_{DM}$ | 174 | A |
| Operating Junction and Storage Temperature | | | $T_J$, $T_{STG}$ | –55 to +175 | °C |
| Source Current (Body Diode) | | | $I_S$ | 72 | A |
| Single Pulse Drain–to–Source Avalanche Energy ($T_J$ = 25°C, $I_L$ = 29 $A_{pk}$, L = 0.1 mH) | | | $E_{AS}$ | 42 | mJ |
| Lead Temperature for Soldering Purposes (1/8″ from case for 10 s) | | | $T_L$ | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Surface–mounted on FR4 board using 650 $mm^2$, 2 oz Cu pad.
3. Assumes heat–sink sufficiently large to maintain constant case temperature independent of device power.
4. Continuous DC current rating. Maximum current for pulses as long as one second is higher but dependent on pulse duration and duty cycle.

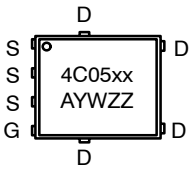



**SO–8 FL**
**CASE 488AA**



**DFNW5**
**CASE 507BE**

**MARKING DIAGRAM**




4C05N = Specific Device Code for NVMFS4C05N
4C05WF= Specific Device Code of NVMFS4C05NWF
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceabililty

### ORDERING INFORMATION

| Device | Package | Shipping† |
|---|---|---|
| NVMFS4C05NT1G, NVMFS4C305NT1G–YE, NVMFS4C305NET1G–YE | SO–8 FL (Pb–Free) | 1500 / Tape & Reel |
| NVMFS4C05NT3G | SO–8 FL (Pb–Free) | 5000 / Tape & Reel |
| NVMFS4C05NWFT1G, NVMFS4C05NWFET1G | DFNW5 (Pb–Free) | 1500 / Tape & Reel |
| NVMFS4C05NWFT3G | DFNW5 (Pb–Free) | 5000 / Tape & Reel |

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## THERMAL RESISTANCE MAXIMUM RATINGS

| Parameter | Symbol | Value | Unit |
|---|---|---|---|
| Junction−to−Case (Drain) | $R_{\theta JC}$ | 1.9 | °C/W |
| Junction−to−Ambient − Steady State (Note 5) | $R_{\theta JA}$ | 41.6 | |

5. Surface−mounted on FR4 board using 650 $mm^2$, 2 oz Cu pad.

## ELECTRICAL CHARACTERISTICS ($T_J$ = 25°C unless otherwise specified)

| Parameter | Symbol | Test Condition | | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | | |
| Drain−to−Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}$ = 0 V, $I_D$ = 250 μA | | 30 | | | V |
| Drain−to−Source Breakdown Voltage Temperature Coefficient | $V_{(BR)DSS}/T_J$ | | | | 12 | | mV/°C |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 24 V | $T_J$ = 25°C | | | 1.0 | μA |
| | | | $T_J$ = 125°C | | | 10 | |
| Gate−to−Source Leakage Current | $I_{GSS}$ | $V_{DS}$ = 0 V, $V_{GS}$ = ±20 V | | | | ±100 | nA |
| **ON CHARACTERISTICS** (Note 6) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(TH)}$ | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | | 1.3 | | 2.2 | V |
| Threshold Temperature Coefficient | $V_{GS(TH)}/T_J$ | | | | −5.1 | | mV/°C |
| Drain−to−Source On Resistance | $R_{DS(on)}$ | $V_{GS}$ = 10 V | $I_D$ = 30 A | | 2.3 | 2.8 | mΩ |
| | | $V_{GS}$ = 4.5 V | $I_D$ = 30 A | | 3.3 | 4.0 | |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$ = 1.5 V, $I_D$ = 15 A | | | 68 | | S |
| Gate Resistance | $R_G$ | $T_A$ = 25°C | | 0.3 | 1.0 | 2.0 | Ω |
| **CHARGES AND CAPACITANCES** | | | | | | | |
| Input Capacitance | $C_{ISS}$ | $V_{GS}$ = 0 V, f = 1 MHz, $V_{DS}$ = 15 V | | | 1972 | | pF |
| Output Capacitance | $C_{OSS}$ | | | | 1215 | | |
| Reverse Transfer Capacitance | $C_{RSS}$ | | | | 59 | | |
| Capacitance Ratio | $C_{RSS}/C_{ISS}$ | $V_{GS}$ = 0 V, $V_{DS}$ = 15 V, f = 1 MHz | | | 0.030 | | |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 15 V; $I_D$ = 30 A | | | 14 | | nC |
| Threshold Gate Charge | $Q_{G(TH)}$ | | | | 3.3 | | |
| Gate−to−Source Charge | $Q_{GS}$ | | | | 6.0 | | |
| Gate−to−Drain Charge | $Q_{GD}$ | | | | 5.0 | | |
| Gate Plateau Voltage | $V_{GP}$ | | | | 3.1 | | V |
| Total Gate Charge | $Q_{G(TOT)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 15 V; $I_D$ = 30 A | | | 30 | | nC |
| **SWITCHING CHARACTERISTICS** (Note 7) | | | | | | | |
| Turn−On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = 4.5 V, $V_{DS}$ = 15 V, $I_D$ = 15 A, $R_G$ = 3.0 Ω | | | 11 | | ns |
| Rise Time | $t_r$ | | | | 32 | | |
| Turn−Off Delay Time | $t_{d(OFF)}$ | | | | 21 | | |
| Fall Time | $t_f$ | | | | 7.0 | | |
| Turn−On Delay Time | $t_{d(ON)}$ | $V_{GS}$ = 10 V, $V_{DS}$ = 15 V, $I_D$ = 15 A, $R_G$ = 3.0 Ω | | | 8.0 | | ns |
| Rise Time | $t_r$ | | | | 26 | | |
| Turn−Off Delay Time | $t_{d(OFF)}$ | | | | 26 | | |
| Fall Time | $t_f$ | | | | 5.0 | | |
| **DRAIN−SOURCE DIODE CHARACTERISTICS** | | | | | | | |
| Forward Diode Voltage | $V_{SD}$ | $V_{GS}$ = 0 V, $I_S$ = 10 A | $T_J$ = 25°C | | 0.77 | 1.1 | V |
| | | | $T_J$ = 125°C | | 0.62 | | |
| Reverse Recovery Time | $t_{RR}$ | $V_{GS}$ = 0 V, $dI_S/dt$ = 100 A/μs, $I_S$ = 30 A | | | 40.2 | | ns |
| Charge Time | $t_a$ | | | | 20.3 | | |
| Discharge Time | $t_b$ | | | | 19.9 | | |
| Reverse Recovery Charge | $Q_{RR}$ | | | | 30.2 | | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
7. Switching characteristics are independent of operating junction temperatures.

## TYPICAL CHARACTERISTICS

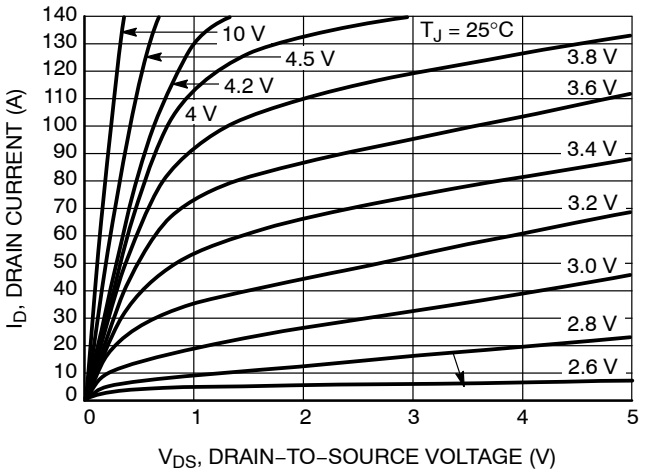



**Figure 1. On−Region Characteristics**

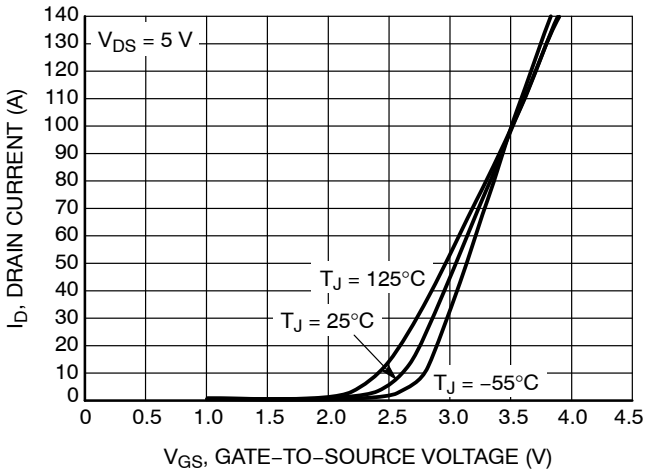



**Figure 2. Transfer Characteristics**

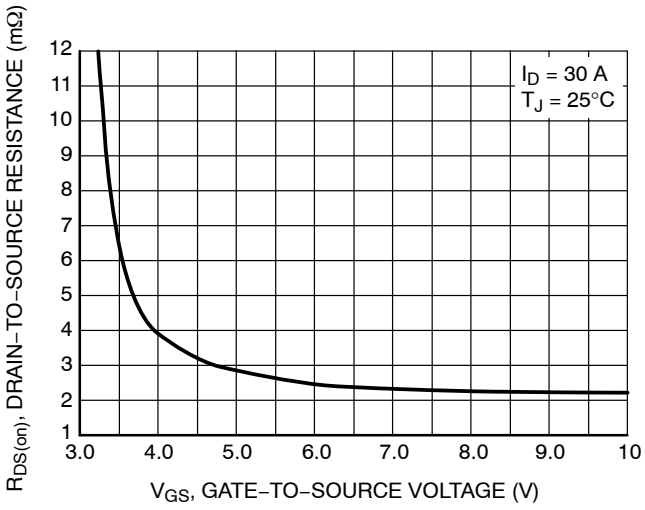



**Figure 3. On−Resistance vs. $V_{GS}$**

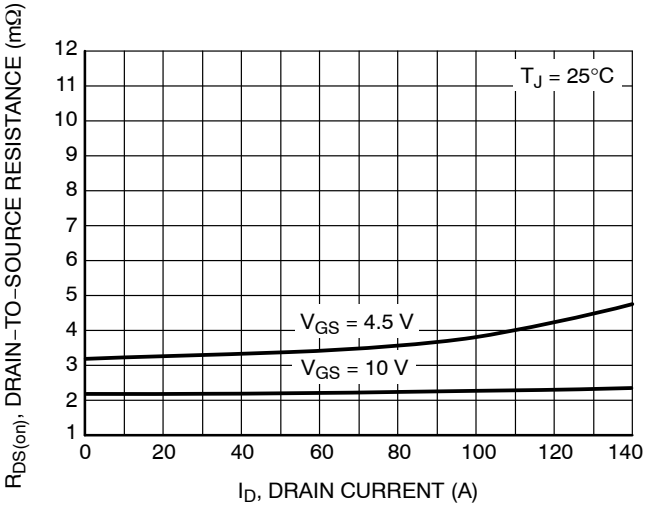



**Figure 4. On−Resistance vs. Drain Current and Gate Voltage**

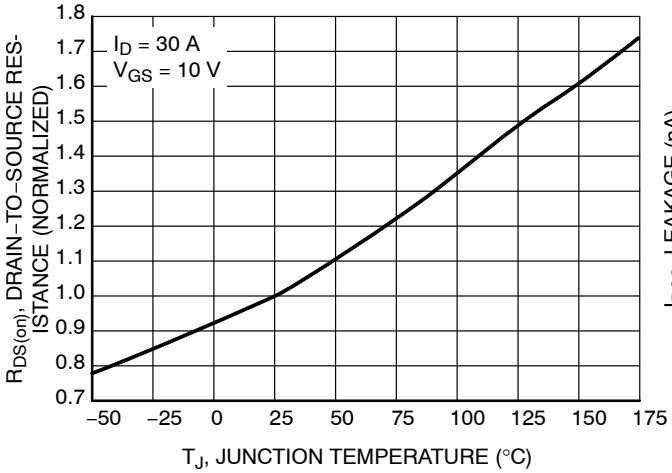



**Figure 5. On−Resistance Variation with Temperature**

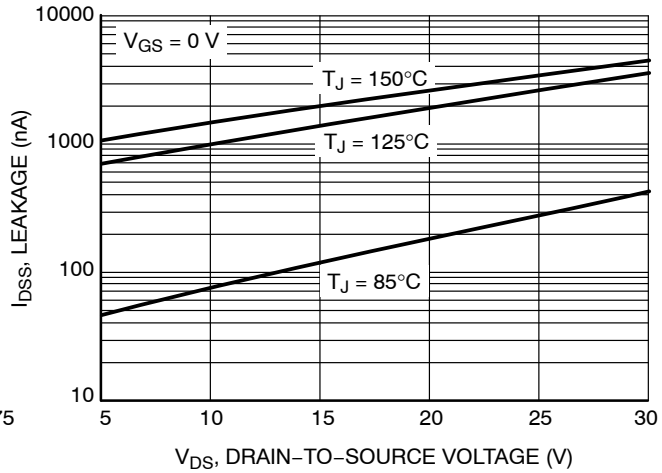



**Figure 6. Drain−to−Source Leakage Current vs. Voltage**

## TYPICAL CHARACTERISTICS

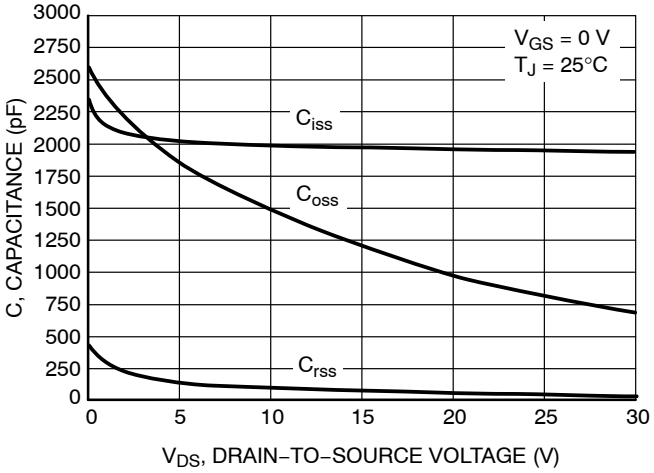



**Figure 7. Capacitance Variation**

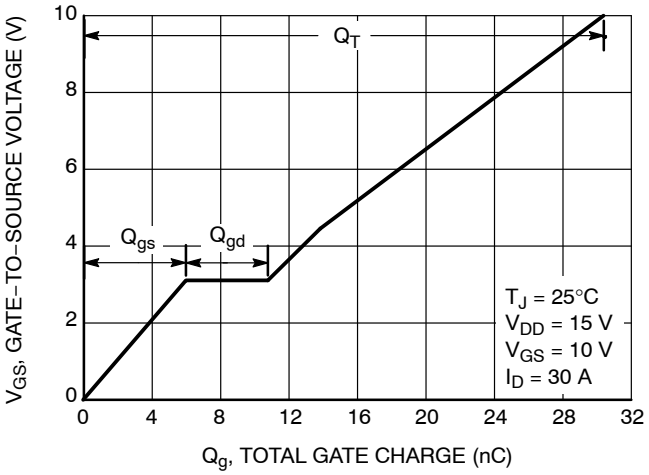



**Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge**

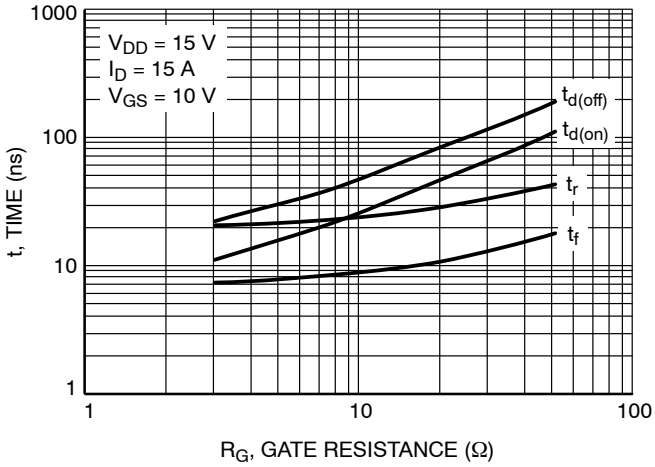



**Figure 9. Resistive Switching Time Variation vs. Gate Resistance**

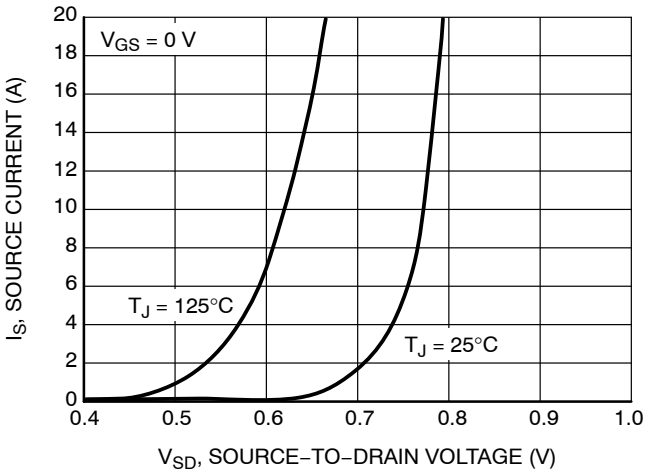



**Figure 10. Diode Forward Voltage vs. Current**

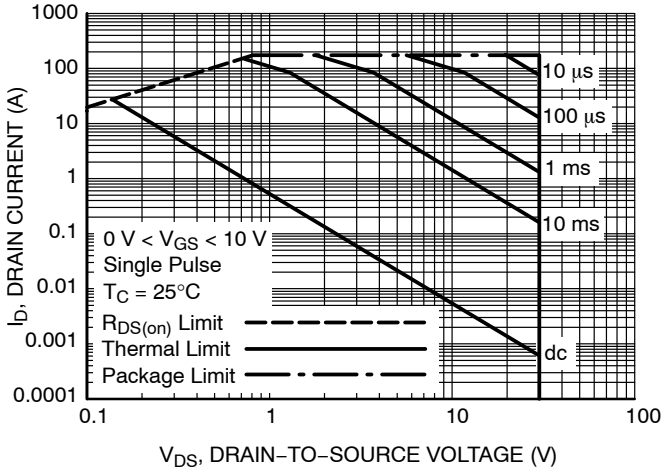



**Figure 11. Maximum Rated Forward Biased Safe Operating Area**

## TYPICAL CHARACTERISTICS

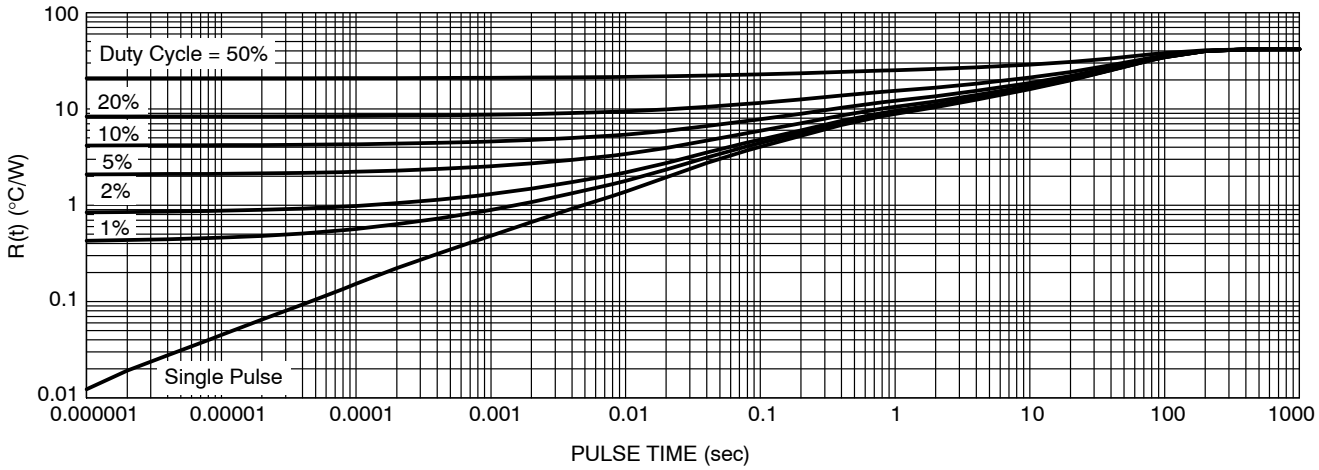



**Figure 12. Thermal Response**

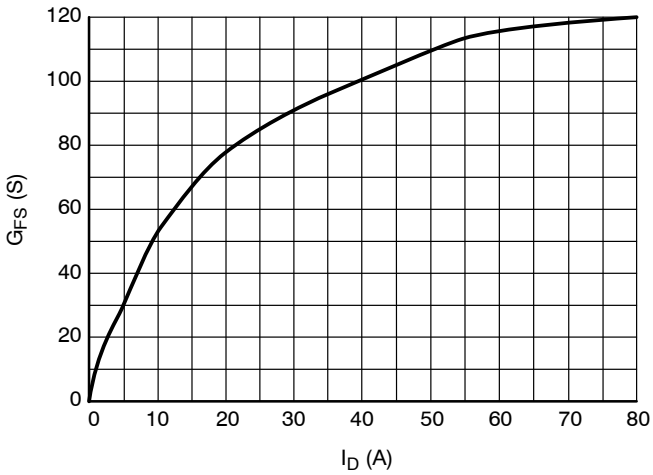



**Figure 13. $G_{FS}$ vs. $I_D$**

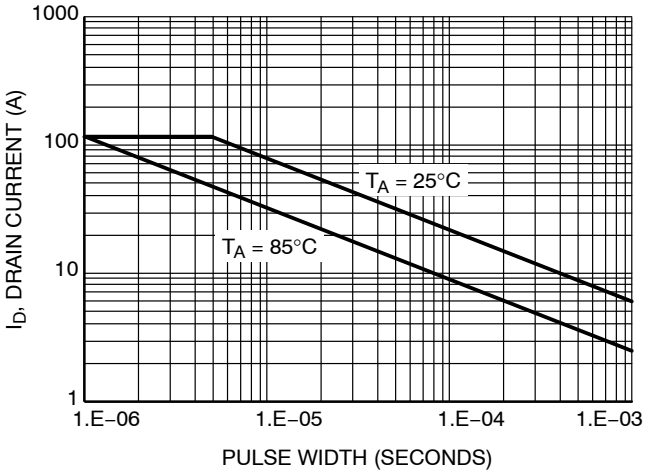
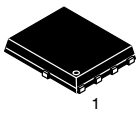


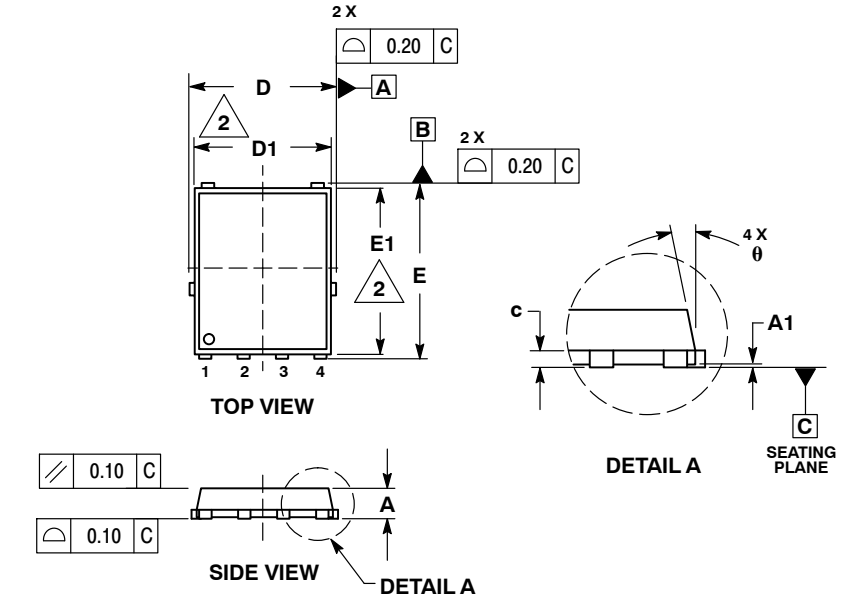

**Figure 14. Avalanche Characteristics**



**SCALE 2:1**

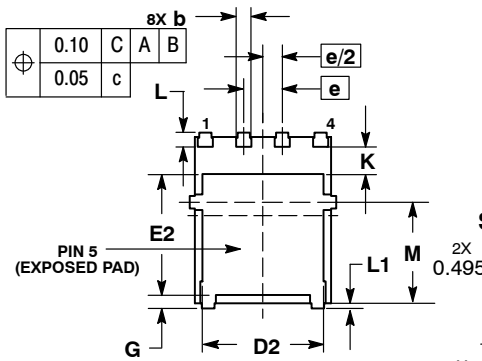
**DFN5 5x6, 1.27P**
**(SO−8FL)**
CASE 488AA
ISSUE N

DATE 25 JUN 2018

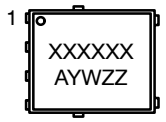



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

| | MILLIMETERS | | |
|---|---|---|---|
| DIM | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | ––– | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.575 | 0.71 |
| K | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.575 | 0.71 |
| L1 | 0.125 REF | | |
| M | 3.00 | 3.40 | 3.80 |
| θ | 0 ° | ––– | 12 ° |



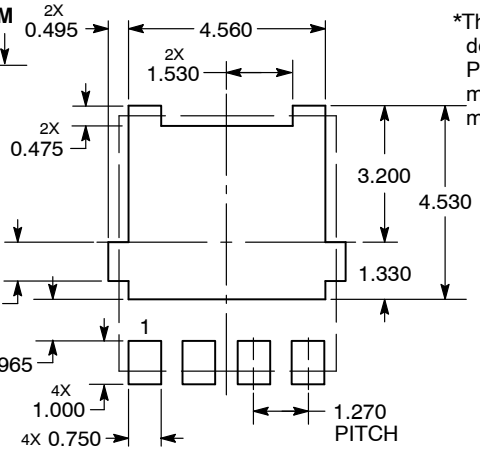

**GENERIC MARKING DIAGRAM***




XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

**RECOMMENDED SOLDERING FOOTPRINT***



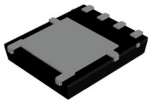

DIMENSIONS: MILLIMETERS

STYLE 1:
PIN 1. SOURCE
2. SOURCE
3. SOURCE
4. GATE
5. DRAIN

STYLE 2:
PIN 1. ANODE
2. ANODE
3. ANODE
4. NO CONNECT
5. CATHODE

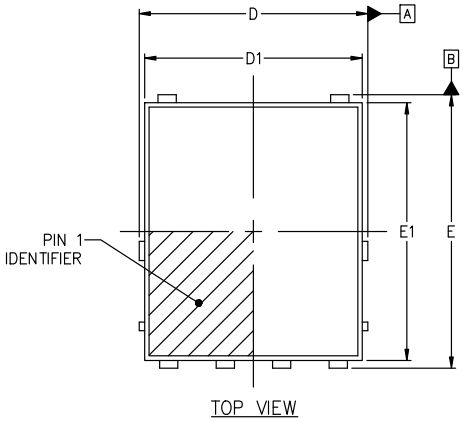
*For additional information on our Pb−Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

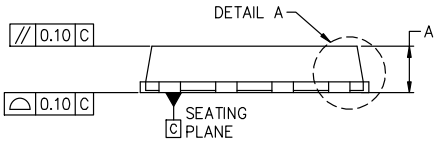
| | | | |
|---|---|---|---|
| **DOCUMENT NUMBER:** | **98AON14036D** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. | |
| **DESCRIPTION:** | **DFN5 5x6, 1.27P (SO−8FL)** | | **PAGE 1 OF 1** |

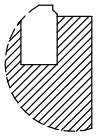


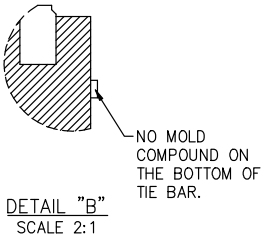
**DFNW5 4.90x5.90x1.00, 1.27P**
CASE 507BE
ISSUE B

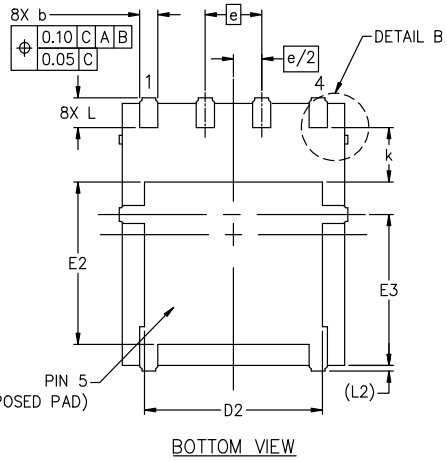
DATE 19 SEP 2024



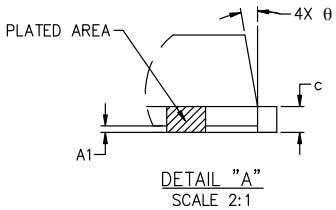



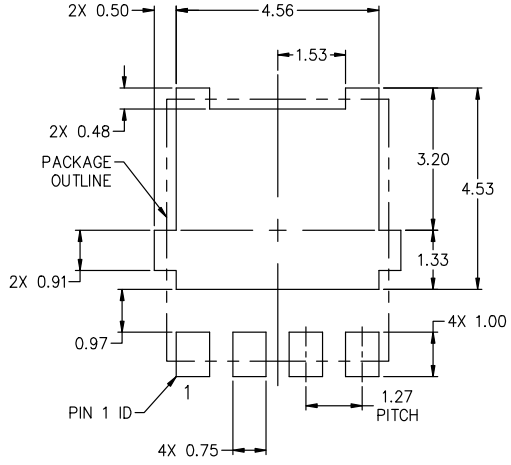




NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5M−2018.
2. ALL DIMENSIONS ARE IN MILLIMETERS.
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

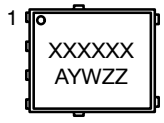



| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 0.90 | 1.00 | 1.10 |
| A1 | 0.00 | --- | 0.05 |
| b | 0.33 | 0.41 | 0.51 |
| c | 0.23 | 0.28 | 0.33 |
| D | 5.00 | 5.15 | 5.30 |
| D1 | 4.70 | 4.90 | 5.10 |
| D2 | 3.80 | 4.00 | 4.20 |
| E | 6.00 | 6.15 | 6.30 |
| E1 | 5.70 | 5.90 | 6.10 |
| E2 | 3.45 | 3.65 | 3.85 |
| E3 | 3.00 | 3.40 | 3.80 |
| e | 1.27 BSC | | |
| k | 1.20 | 1.35 | 1.50 |
| L | 0.51 | 0.57 | 0.71 |
| L2 | 0.15 REF. | | |
| θ | 0° | 6° | 12° |




RECOMMENDED MOUNTING FOOTPRINT*
*FOR ADDITIONAL INFORMATION ON OUR Pb−FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ONSEMI SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM***




XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot " ▪", may or may not be present. Some products may not follow the Generic Marking.

| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON33319H** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. |
| **DESCRIPTION:** | **DFNW5 4.90x5.90x1.00, 1.27P** | **PAGE 1 OF 1** |

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

**ONLINE SUPPORT**: www.onsemi.com/support
**For additional information, please contact your local Sales Representative at** www.onsemi.com/support/sales